2018년 2월 7일(수), 16:15-17:30 Room G (봉래II+III, 6층)

G. Device & Process Modeling, Simulation and Reliability 분과 [WG4-G] Memory and TFT - Modeling and Characterization

좌장: 나현철 수석(DB 하이텍), 홍성민 교수(GIST)

WG4-G-1 16:15-16:30	TCAD Modeling of Endurance and Retention in NAND Flash Device Dongyean Oh, Bonghoon Lee, Eunmee Kwon, Sangyong Kim, Sungkye Park, Seong-Dong Kim, Seokkiu Lee, and Sungjoo Hong Research and Development Division, SK Hynix Incorporated
WG4-G-2 16:30-16:45	유한요소법을 이용한 저항 메모리의 정전기적 거동에 대한 시뮬레이션 민경환, 권용우 Department of Material science and Engineering., Hongik University
WG4-G-3 16:45-17:00	Study on Negative Bias Stress-Induced Instability in Zinc Oxynitride Thin-Film Transistors Using Systematic Decomposition Hye Ri Yu, Jun Tae Jang, Geumho Ahn, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim School of Electrical Engineering, Kookmin University
WG4-G-4 17:00-17:15	Extraction Method of Temperature-Independent Subgap Density-of-States of a-IGZO TFTs by Using Fermi-Dirac Distribution Sungju Choi, Jae-Young Kim, Jaewon Kim, Jihyun Rhee, Hye Ri Yu, Hara Kang, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim School of Electrical Engineering, Kookmin University
WG4-G-5 17:15-17:30	High-Temperature Characteristic of Low-Temperature Polycrystalline SiliconThin-Film Transistors (LTPS-TFTs) on Glass and Plastic Substrates Soo Hyun Kim, Dong Hyun Kim, Kwan Hyun Cho, Dong Geun Park, and Jae Woo Lee ICT Convergence Technology for Health & Safety and Department of Electronics and Information Engineering, Korea University